

Film-thickness dependence of 10 GHz Nb coplanar-waveguide resonators

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We have studied Nb $\lambda/2$ coplanar-waveguide (CPW) resonators whose resonant frequencies are 10 – 11 GHz. The resonators have different film thicknesses, $t = 0.05, 0.1, 0.2$, and $0.3 \mu\text{m}$. We measured at low temperatures, $T = 0.02 - 5 \text{ K}$, one of the scattering-matrix element, S_{21} , which is the transmission coefficient from one port to the other. At the base temperatures, $T = 0.02 - 0.03 \text{ K}$, the resonators are overcoupled to the input/output microwave lines, and the loaded quality factors are on the order of 10^3 . The resonant frequency has a considerably larger film-thickness dependence compared to the predictions by circuit simulators which calculate the inductance of CPW taking into account L_g only, where L_g is the usual magnetic inductance determined by the CPW geometry. By fitting a theoretical S_{21} vs. frequency curve to the experimental data, we determined for each film thickness, the phase velocity of the CPW with an accuracy better than 0.1%. The large film-thickness dependence must be due to the kinetic inductance L_k of the CPW center conductor. We also measured S_{21} as a function of temperature up to $T = 4 - 5 \text{ K}$, and confirmed that both thickness and temperature dependence are consistent with the theoretical prediction for L_k .

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I. INTRODUCTION

Microwave resonators (for example, Chap. 7 of Ref. 1) are one of the key components in a variety of circuits operated at GHz frequencies, and their new applications continue to emerge. A simple example is band-pass filters, which are based on the fact that the microwave transmission through resonators is frequency sensitive. The same idea is also used for more complex devices, such as oscillators, tuned amplifiers, and frequency meters. Actually, having high-quality filters and oscillators is critical in mobile communications, where available bands keep getting overcrowded as demand grows rapidly.

Another application of microwave resonators is radiation detectors, which often consist of sensor heads and read-out circuits, and resonators can be used in the readout circuit. When one would like to detect at the single-photon level, one needs to have detectors with high enough energy resolutions. In this respect, superconducting sensor heads^{2,3,4} can be advantageous, and may be the only solution at present depending on the energy range of the object. Once one decides to use superconducting sensor heads, it makes sense to fabricate the read-out circuit with superconducting materials as well. Superconducting microwave resonators allow one to obtain higher quality factors, which are favorable for frequency multiplexing. In addition, one type of photon detector is designed to probe the change in the kinetic inductance of superconducting thin-film resonator due to the absorbed photons.⁵ In this device concept, the resonator works as a sensor head rather than a part of the readout circuit.

Recently, superconducting resonators are used for the nondemolition readout of superconducting qubits as

well.⁶ Since the demonstration by Wallraff *et al.*,⁶ this type of readout scheme has been one of the main topics in the field of superconducting qubits, and we are also developing a similar readout technique.⁷ In superconducting resonators, kinetic inductance, which is essentially the internal mass of the current carriers, plays an important role especially when the superconducting film is thin. In our circuit,⁷ for example, a Nb $\lambda/4$ coplanar-waveguide (CPW) resonator is terminated by an Al dc SQUID, and the total thickness of the Al layers is $0.04 \mu\text{m}$. In order to avoid a discontinuity at the Al/Nb interface, we usually choose the Nb thickness to be $0.05 \mu\text{m}$, which is much thinner than a typical thickness of $\geq 0.3 \mu\text{m}$ for superconducting integrated circuits fabricated by the standard photolithographic technology. Fabricating circuits with thinner films is actually important from the viewpoint of miniaturization as well. Therefore, for designing resonators, quantitative understanding of the kinetic inductance in the CPW is important.

There have been a number of reports on kinetic inductance for a variety of materials.^{8,9,10,11,12,13} In general, however, kinetic inductance is indirectly measured by assuming a theoretical model, and as a result, the uncertainties are relatively large. Thus, although kinetic inductance is a well established notion and the phenomenon is qualitatively understood, the quantitative information is not necessarily sufficient from the point of view of applications, especially at high frequencies, $>10 \text{ GHz}$. When we would like to precisely predict the resonant frequency, the best solution would be to characterize the actual CPW in a simple circuit. Such characterization should also improve the knowledge of superconducting microwave circuits. Very recently, Göppl *et al.*¹⁴ measured a series of Al CPW resonators with nominally the same film thickness of $0.2 \mu\text{m}$, and investigated

TABLE I: List of resonators. t is the thickness of Nb film; f_r is the resonant frequency; Q_L is the unloaded quality factor; C_c is the coupling capacitance; v_p is the phase velocity, and its ratio to the speed of light c is listed in percent. The values for f_r and Q_L are obtained at the base temperatures. C_c and v_p are evaluated by least-squares fitting (see Fig. 4) with $C = 1.6 \times 10^{-10}$ F/m, and their uncertainties are determined by changing the value of C by $\pm 10\%$, where C is the capacitance per unit length.

Reso-nator	t (μm)	f_r (GHz)	Q_L ($\times 10^3$)	C_c (fF)	v_p/c (%)
A1	0.05	10.01	1.6	7.0 ± 0.4	39.31 ± 0.03
A2	0.1	10.50	1.4	7.3 ± 0.4	41.28 ± 0.04
A3	0.2	10.74	1.4	7.2 ± 0.4	42.21 ± 0.04
A4	0.3	10.88	1.6	6.6 ± 0.4	42.71 ± 0.03
B1	0.05	10.06	3.4	4.6 ± 0.3	39.32 ± 0.02
B2	0.1	10.56	3.1	4.8 ± 0.3	41.26 ± 0.02
B3	0.2	10.81	2.7	5.0 ± 0.3	42.27 ± 0.03
B4	0.3	10.94	3.3	4.5 ± 0.3	42.72 ± 0.02

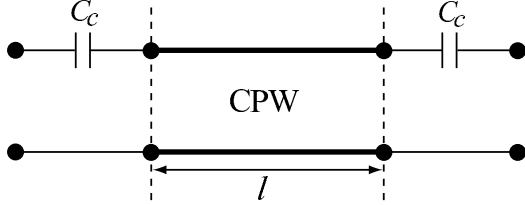


FIG. 1: Schematic diagram of coplanar-waveguide (CPW) resonators. A CPW of length l is coupled to the microwave lines through capacitors C_c .

the relationship between the loaded quality factor at the base temperature of 0.02 K and the coupling capacitance. For this purpose, it is justified to neglect kinetic inductance because the kinetic inductance should be the same in their resonators and estimated¹⁴ to be about two orders of magnitude smaller than the usual magnetic inductance determined by the CPW geometry. In this work, on the other hand, we paid close attention to the resonant frequency as well, and characterized Nb CPW resonators as a function of film thickness rather than a function of coupling capacitance. We also looked at the temperature dependence in order to discuss kinetic inductance in detail.

II. EXPERIMENT

We studied two series of Nb $\lambda/2$ CPW resonators listed in Table I. Each resonator consists of a section of CPW and coupling capacitors, as shown schematically in Fig. 1. The resonators were fabricated on a nominally undoped Si wafer whose surface had been thermally oxidized. On the SiO_2/Si substrate, a Nb film was deposited by sputtering and then patterned by photolithography and SF_6 reactive ion etching. Figure 2(a) represents the cross

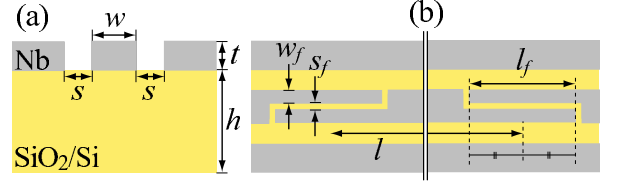


FIG. 2: (Color online) (a) Cross section of a coplanar waveguide. (b) Top view of coupling capacitors.

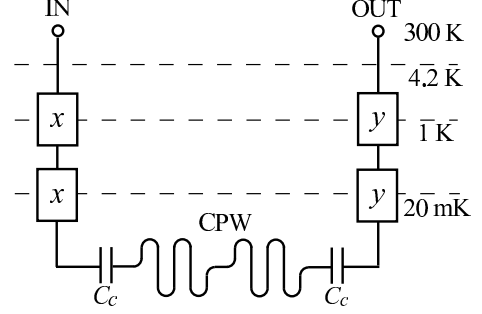


FIG. 3: Schematic diagram of a typical measurement setup. Boxes represent attenuators.

section of CPW. The center conductor has a width of $w = 10 \mu\text{m}$, and separated from the the ground planes by $s = 5.8 \mu\text{m}$, so that the characteristic impedance becomes $\sim 50 \Omega$. The thickness of Nb is $t = 0.05, 0.1, 0.2$, or $0.3 \mu\text{m}$ (see Table I), and that of SiO_2/Si substrate is $h = 300 \mu\text{m}$. The SiO_2 layer, whose thickness is $0.3 \mu\text{m}$, is not drawn in Fig. 2(a). We employed interdigital coupling capacitors as shown in Fig. 2(b). The finger width is $w_f = 9 \mu\text{m}$, the space between the fingers is $s_f = 2 \mu\text{m}$, and the finger length is $l_f = 78 \mu\text{m}$ for Resonators A1–A4 and $l_f = 38 \mu\text{m}$ for Resonators B1–B4. Here, we quoted designed dimensions for the Nb structures. The actual dimensions differ by about $0.2 \mu\text{m}$ due to over-etching; for example, w and w_f are $\sim 0.2 \mu\text{m}$ smaller, whereas s and s_f are $\sim 0.2 \mu\text{m}$ larger. In this paper, we define the resonator length l as the distance between the center of the fingers on one side and that on the other side, and $l = 5.8 \text{ mm}$ for all resonators. Because our chip size is 2.5 mm by 5.0 mm , our CPWs meander as in Fig. 3.

The resonators were measured in a ^3He - ^4He dilution refrigerator at $T = 0.02$ – 5 K . A typical measurement setup is shown schematically in Fig. 3. The boxes in the figure represent attenuators. The amount of attenuation was not the same because the microwave lines in our refrigerator had been designed for several different purposes. The attenuation was $x = 10 \text{ dB}$ for Resonators A2, B3, and B4, and $x = 20 \text{ dB}$ for the others; $y = 10 \text{ dB}$ for all resonators except A1 and A3. For Resonators A1 and A3, we used a line with no attenuators ($y = 0 \text{ dB}$) but with an isolator and a cryogenic amplifier at 4.2 K . The gain of the cryogenic amplifier was 40 dB for Resonator A1 and 34 dB for A3. We measured the transmission coefficient

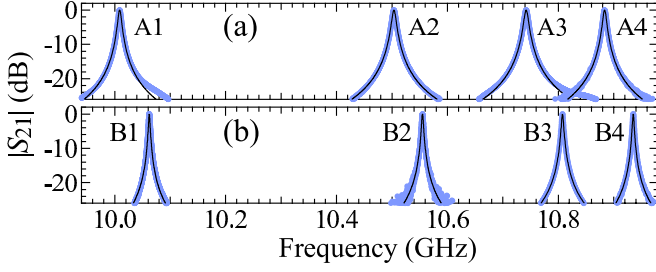


FIG. 4: (Color online) Amplitude of the transmission coefficient S_{21} as a function of frequency for (a) Resonators A1–A4, and (b) Resonators B1–B4.

S_{21} by connecting a vector network analyzer to the “IN” and “OUT” ports in Fig. 3. A typical incident power to the resonator was -40 dBm. For each resonator, we confirmed that the measurements were done in an appropriate power range in the sense that the results looked power independent.

III. RESULTS

A. S_{21} at the base temperatures

Figure 4 shows the amplitude of S_{21} at the base temperatures, $T = 0.02 - 0.03$ K, as a function of frequency f for all resonators. The resonant frequency f_r has a rather large film-thickness dependence. Our interpretation is that this is due to the kinetic inductance of the CPW center conductor. Before discussing the thickness dependence in detail, let us look at the quality factors.

What we obtain by measuring S_{21} as a function of f is the loaded quality factor Q_L , which is related to the external quality factor Q_e and the unloaded quality factor Q by

$$Q_L^{-1} = Q_e^{-1} + Q^{-1}. \quad (1)$$

In general, Q_e is determined mainly by C_c , whereas Q is a measure of the internal loss, which arises not only from the dielectric but also from the superconductor in the high-frequency regime. Our resonators should be highly overcoupled to the input/output lines at the base temperatures, that is, $Q \gg Q_e$, and thus, $Q_L \sim Q_e$. As listed in Table I, Q_L of our resonators is on the order of 10^3 . These values are not only reasonable for the designs of our finger-shaped coupling capacitors but also much smaller than typical values of Q below 0.1 K for superconducting microwave resonators.^{5,13,14} When $Q \gg Q_e$, the maximum $|S_{21}|$ is expected to be 0 dB. We have confirmed by taking into account attenuators, amplifiers, and cable losses, that our measurements are indeed consistent within the uncertainties of gain/loss calculations, $1-2$ dB. Based on this confirmation, the experimental data in Fig. 4 are normalized so that the peak heights equal 0 dB.

The solid curves in Fig. 4 are calculations based on the transmission ($ABCD$) matrix (for example, Sec. 5.5 of Ref. 1), and they reproduce the experimental data well. The matrix for the resonators is given by

$$\begin{pmatrix} A & B \\ C & D \end{pmatrix} = T_{cc} T_{cpw} T_{cc}, \quad (2)$$

where

$$T_{cc} = \begin{pmatrix} 1 & (j\omega C_c)^{-1} \\ 0 & 1 \end{pmatrix}, \quad (3)$$

j is the imaginary unit,

$$T_{cpw} = \begin{pmatrix} \cos \beta l & jZ_{cpw} \sin \beta l \\ j(Z_{cpw})^{-1} \sin \beta l & \cos \beta l \end{pmatrix} \quad (4)$$

for lossless CPWs, $\omega = 2\pi f$, $\beta = \omega/v_p$,

$$v_p = 1/\sqrt{LC} \quad (5)$$

is the phase velocity, which is strongly related to f_r ,

$$Z_{cpw} = \sqrt{L/C} \quad (6)$$

is the characteristic impedance, L is the inductance per unit length, and C is the capacitance per unit length. From these transmission-matrix elements, the scattering-matrix elements are calculated, and S_{21} is given by

$$S_{21} = 2/(A + B/Z_0 + CZ_0 + D), \quad (7)$$

where $Z_0 = 50 \Omega$ is the characteristic impedance of the microwave lines connected to the resonator. Unit-length properties of CPW are determined when two parameters out of v_p , Z_{cpw} , L , and C are specified. In the calculations for Fig. 4, we employed $C = 1.6 \times 10^{-10}$ F/m based on the considerations described in the following paragraph, and evaluated C_c and v_p by least-squares fitting.

Wen¹⁵ calculated CPW parameters using conformal mapping. Within the theory, C does not depend on t , and it is given by

$$C = (\epsilon_r + 1)\epsilon_0 2K(k)/K(k'), \quad (8)$$

where ϵ_r is the relative dielectric constant of the substrate, $\epsilon_0 = 8.85 \times 10^{-12}$ F/m is the permittivity of free space, $K(k)$ is the complete elliptical integral of the first kind, the argument k is given by

$$k = w/(w + 2s), \quad (9)$$

and $k' = \sqrt{1 - k^2}$. For our CPWs, we obtain $C = 1.6 \times 10^{-10}$ F/m when we employ $\epsilon_r = 11.7$ for Si (p. 223 of Ref. 16) neglecting the contribution from the SiO_2 layer, which is much thinner compared to w , s , or h . Circuit simulators [Microwave Office from AWR (#1) and AppCAD from Agilent (#2)] also predict similar values of C . The simulators calculate CPW parameters from

TABLE II: Dependence of coplanar-waveguide parameters on the film thickness t . For capacitance C and inductance L per unit length, the normalized variations $\Delta C(t)/C^*$ and $\Delta L(t)/L^*$ are listed in percent, where $\Delta C(t) = C(t) - C^*$, $C^* \sim 1.6 \times 10^{-10}$ F/m is the value at $t = 0.3 \mu\text{m}$, and the definitions of $\Delta L(t)$ and $L^* \sim 4 \times 10^{-7}$ H/m are similar. The predictions by circuit simulators #1 and #2 are compared. Regarding L , experimental values for “A”=Resonators A1–A4 and for “B”=Resonators B1–B4 are also given, and they are obtained from the values of v_p in Table I using Eq. (5) and by neglecting the t dependence of C .

t (μm)	$\Delta C(t)/C^*$ (%)		$\Delta L(t)/L^*$ (%)			
	#1	#2	#1	#2	A	B
0.05	-0.6	1.7	3.9	2.9	18.0	18.0
0.1	-0.5	1.4	3.0	2.2	7.1	7.2
0.2	-0.2	0.8	1.4	1.2	2.4	2.1

the dimensions and the material used for the substrate. The predictions by the simulators have t dependence, but in the relevant t range, the variations are on the order of 1% or smaller as summarized in Table II, and the values of C are between 1.6×10^{-10} F/m and 1.7×10^{-10} F/m. Thus, partly for simplicity, we used $C = 1.6 \times 10^{-10}$ F/m for all of our resonators.

With $C = 1.6 \times 10^{-10}$ F/m, the values of v_p in Table I correspond to $Z_{\text{cpw}} = 49 - 53 \Omega$, which agrees with our design of $\sim 50 \Omega$. We have done the same fitting by changing the value of C by $\pm 10\%$ as well in order to estimate the uncertainties, which are also listed in Table I. Within the uncertainties, the values of C_c from the same coupling-capacitor design agree, and $C_c \sim 7$ fF for Resonators A1–A4 with $l_f = 78 \mu\text{m}$ and $C_c \sim 5$ fF for Resonators B1–B4 with $l_f = 38 \mu\text{m}$. The uncertainties for v_p is much smaller, $< 0.1\%$, and again within the uncertainties, the values of v_p for the same t agree.

For the rest of this paper, let us assume that t dependence of C is negligible. This assumption is consistent with the fact that the experimental C_c vs. t in Table I does not show any obvious trend. Moreover, according to the circuit simulators in Table II, t dependence of C is smaller than that of L . Below, we look at L mainly instead of v_p or other CPW parameters so that we will be able to discuss the kinetic inductance. As long as we deal with a normalized inductance such as the ratio of $L(t)$ to $L^* \equiv L(0.3 \mu\text{m})$, what we choose for the value of C does not matter very much because v_p obtained from the fitting was not so sensitive to C . Hence, we analyze the quantities obtained with $C = 1.6 \times 10^{-10}$ F/m only hereafter. In Table II, we list the variations of L in our two series of resonators as well. For both series, the magnitude of the variations are much larger than the predictions by circuit simulators. We will discuss this large t dependence in terms of kinetic inductance in Sec. IV after examining the temperature dependence in Sec. III B.

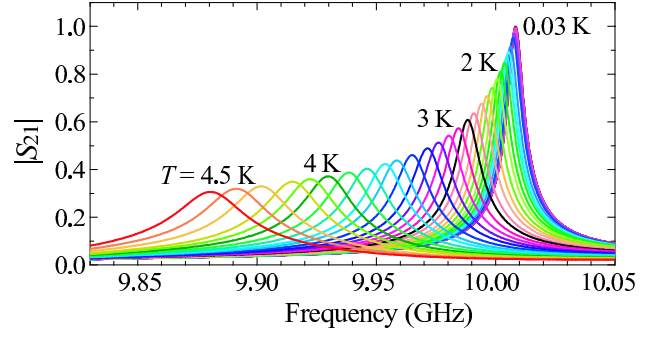


FIG. 5: (Color online) Amplitude of the transmission coefficient S_{21} as a function of frequency for Resonators A1 at different temperatures.

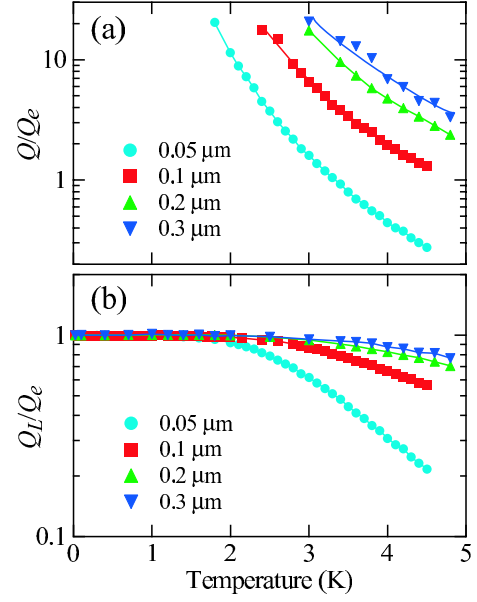


FIG. 6: (Color online) Normalized quality factors, (a) Q/Q_e and (b) Q_L/Q_e , as functions of temperature for Resonators A1–A4 (Nb thickness $t = 0.05, 0.1, 0.2$, and $0.3 \mu\text{m}$), where Q_L , Q_e , and Q are loaded, external, and unloaded quality factors, respectively, and Q_e is assumed to be temperature independent. The markers are data points, whereas the curves are guides to the eyes.

B. Temperature dependence of S_{21}

We also measured S_{21} vs. f at various temperatures up to $T = 4 - 5$ K for Resonators A1–A4. We show the results for Resonator A1 in Fig. 5. With increasing temperature, f_r , Q_L , and the peak height decrease. As in Sec. III A, let us look at the quality factors first. In our resonators, $Q_e \sim Q_L$ at the base temperatures as we pointed out in Sec. III A. Thus, when we assume that Q_e is temperature independent, we can calculate Q from measured Q_L using Eq. (1). We plot $Q_L(T)/Q_e$ and $Q(T)/Q_e$ vs. T in Fig. 6 for all of the four res-

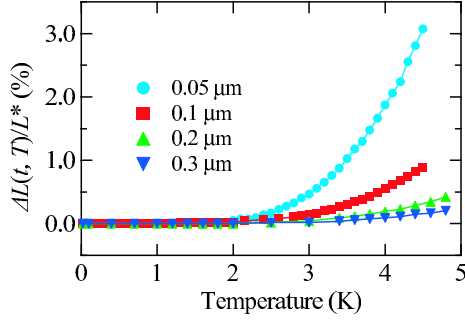


FIG. 7: (Color online) Temperature variations of inductance L per unit length for Resonators A1–A4, whose Nb thickness is $t = 0.05, 0.1, 0.2$, and $0.3 \mu\text{m}$. The unit of the vertical axis is percent. See text for the definition of $\Delta L(t, T)/L^*$.

onators. With increasing temperature, Q decreases in all resonators. A finite Q^{-1} means that the resonator has a finite internal loss, which is consistent with a peak height smaller than unity in Fig. 5. The internal loss at high temperatures must be due to quasiparticles in the superconductor, as discussed in Ref. 5. The reduction of quality factors becomes larger as the Nb thickness is decreased. At $T < 1$ K, however, the reduction is negligibly small, and thus, in this sense, it should be fine to choose any thickness in the range of $t = 0.05 - 0.3 \mu\text{m}$ for the study of superconducting qubits that we mentioned in Sec. I because qubit operations are almost always done at the base temperatures.

When CPWs are no longer lossless, β in Eq. (4) has to be replaced by $(\alpha + j\beta)/j$. This α characterizes the internal loss, and $\beta/(2\alpha)$ is equal to Q (for example, Sec. 7.2 of Ref. 1). From similar calculations to those in Sec. III A, we evaluated L at higher temperatures as well by neglecting the T dependence of C and C_c . Because we are interested in the temperature variation of L , we show $\Delta L(t, T)/L^*$ vs. T in Fig. 7, where $\Delta L(t, T) \equiv L(t, T) - L(t, T^*)$, T^* is the base temperature, and $L^* \equiv L(0.3 \mu\text{m}, T^*)$. The variation becomes larger as the Nb thickness is decreased. This trend also suggests that we should take into account the kinetic inductance.

IV. DISCUSSION

The film-thickness and temperature dependence that we have examined in Sec. III is explained by the model,

$$L(t, T) = L_g(t) + L_k(t, T), \quad (10)$$

where L_g is the usual magnetic inductance per unit length determined by the CPW geometry and L_k is the kinetic inductance of the CPW center conductor per unit length. We neglect the contribution of the ground planes to L_k because the ground planes are much wider than the center conductor in our resonators [see Eq. (11)]. We

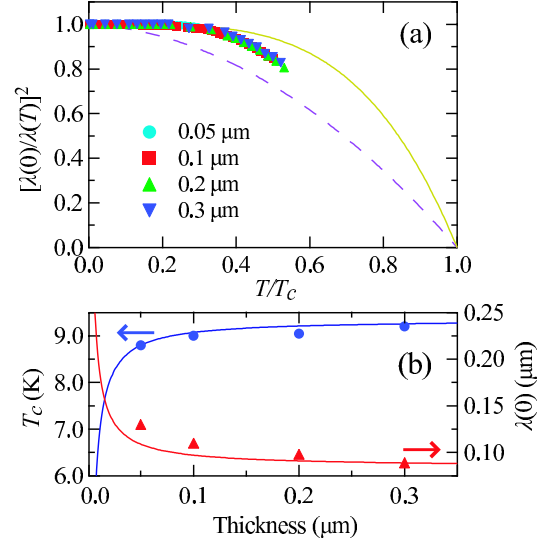


FIG. 8: (Color online) (a) Temperature dependence of the penetration depth λ for Resonators A1–A4, whose Nb thickness is $t = 0.05, 0.1, 0.2$, and $0.3 \mu\text{m}$. The solid and broken curves are theoretical predictions expressed by Eqs. (12) and (13), respectively. As in Ref. 17, $[\lambda(t, 0)/\lambda(t, T)]^2$ is plotted vs. $T/T_c(t)$. (b) Superconducting transition temperature $T_c(t)$ used in (a), and $\lambda(t, 0)$. The curves are from Ref. 12, that is, not fitted to our experimental data. Both in (a) and (b), $\lambda(T^*) \sim \lambda(0)$ is assumed, where T^* is the base temperature.

also assume that L_g depends on t only, whereas L_k does on both t and T . This type of model has been employed in earlier works^{9,13,14} as well. The T dependence of L_k arises from the fact that L_k is determined not only by the geometry but also by the penetration depth λ , which varies with T . Meservey and Tedrow⁸ calculated L_k of a superconducting strip, and when the strip has a rectangular cross section like our CPWs, L_k is written as

$$L_k = \frac{\mu_0}{\pi^2} (\lambda/w) \ln(4w/t) \frac{\sinh(t/\lambda)}{\cosh(t/\lambda) - 1}, \quad (11)$$

where $\mu_0 = 4\pi \times 10^{-7}$ H/m is the permeability of free space. The relationship between L_k and λ is expressed in a much simpler form in the thick- and thin-film limits; $L_k \propto \lambda$ for $t \gg \lambda$, and $L_k \propto \lambda^2$ for $t \ll \lambda$. When we assume Eqs. (10) and (11), we obtain $\lambda(t, T)$ numerically, once $L_g(t)$ is given. Below, we discuss $\lambda(t, T)$ in our Nb films in order to confirm that the model represented by Eq. (10) is indeed appropriate.

In Fig. 8(a), we plot $[\lambda(t, T^*)/\lambda(t, T)]^2$ vs. $T/T_c(t)$ for Resonators A1–A4, where $T_c(t)$ is the superconducting transition temperature, which is assumed to be also t dependent in this paper. We have found that with a reasonable set of parameters, $L_g(t)$ and $T_c(t)$, the experimental data for all resonators are described by a single curve. This kind of scaling is expected theoretically in the limits of $\xi_0/\lambda_L \gg 1$ and $\xi_0/\lambda_L \ll 1$, where ξ_0 is the coherence length and λ_L is the London penetration

TABLE III: Inductance per unit length at the base temperatures in Resonators A1–A4. t is the thickness of Nb film; $\Delta L_g(t) = L_g(t) - L_g^*$, where L_g is the usual magnetic inductance per unit length determined by the CPW geometry, and $L_g^* \equiv L_g(0.3 \mu\text{m}) = 3.75 \times 10^{-7} \text{ H/m}$; L_k is the kinetic inductance per unit length, and $L = L_g + L_k$.

t (μm)	$\Delta L_g(t)/L_g^*$ (%)	L_k/L (%)
0.05	4.3	13.1
0.1	3.4	4.9
0.2	1.7	2.2
0.3	–	1.6

depth.¹⁷ Although $\xi_0/\lambda_L \sim 1$ in Nb (p. 353 of Ref. 16) at temperatures well below T_c , it would be still reasonable to expect a scaling in our Nb resonators because at a given normalized temperature $T/T_c(t)$, the relevant quantities should be on the same order of magnitude in all resonators, and thus, two parameters, $\lambda(t, T^*)$ and $T_c(t)$, are probably enough for characterizing $\lambda(t, T)$ of our resonators. The values of $L_g(t)$ and $T_c(t)$ employed in Fig. 8(a) are summarized in Table III and Fig. 8(b), respectively. The relative change of $L_g(t)$ in Table III is similar to the predictions by circuit simulators in Table II, which do not take into account the kinetic inductance. The magnitude of $L_g(t)$ is also reasonable because $\sqrt{L_g(t)/C} \sim 49 \Omega$ for all thickness. In Table III, we also list the ratio of kinetic inductance L_k to the total inductance L . With decreasing thickness, L_k/L indeed increases rapidly. In Fig. 8(b), $T_c(t)$ and $\lambda(t, T^*)$ are plotted together with the theoretical curves in Figs. 1 and 6 of Ref. 12, where Gubin *et al.*¹² determined some parameters of the curves by fitting to their experimental data. The values of $T_c(t)$ are reasonable, and $\lambda(t, T^*)$ is on the right order of magnitude.

The solid curve in Fig. 8(a) is the theoretical T dependence based on the two-fluid approximation,¹⁷

$$[\lambda(0)/\lambda(T)]^2 = 1 - (T/T_c)^4. \quad (12)$$

This theoretical curve reproduces the experimental data at $T/T_c < 0.4$, when we assume that $\lambda(t, T^*) \sim \lambda(t, 0)$ in Resonators A1–A4. At $T/T_c \geq 0.4$, on the other hand, the experimental data deviate from Eq. (12), but according to Ref. 17, the expression for λ vs. T depends on the

ratio of ξ_0/λ_L , and thus, Eq. (12) cannot be expected to apply to all materials equally well. Indeed, although the temperature dependence of Eq. (12) has been observed in the classic pure superconductors,¹⁷ such as Al with $\xi_0/\lambda_L \gg 1$ at temperatures well below T_c , it does not seem to be the case in the high- T_c materials, whose typical ξ_0/λ_L is in the opposite limit,¹⁷ $\xi_0/\lambda_L \ll 1$, and for example, Rauch *et al.*⁹ employed for a high- T_c material $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$, an empirical expression of

$$[\lambda(0)/\lambda(T)]^2 = 1 - 0.1(T/T_c) - 0.9(T/T_c)^2, \quad (13)$$

which is the broken curve in Fig. 8(a), instead. Because $\xi_0/\lambda_L \sim 1$ in Nb even at $T/T_c \ll 1$, and because the experimental data at $T/T_c \geq 0.4$ are between Eqs. (12) and (13), we believe that the deviation from Eq. (12) at $T/T_c \geq 0.4$ is reasonable.

From the discussion in this section, we conclude that the model represented by Eq. (10) explains the film-thickness and temperature dependence of our resonators.

V. CONCLUSION

We investigated two series of Nb $\lambda/2$ CPW resonators with resonant frequencies in the range of 10 – 11 GHz and with different Nb-film thicknesses, 0.05 – 0.3 μm . We measured the transmission coefficient S_{21} as a function of frequency at low temperatures, $T = 0.02 - 5 \text{ K}$. For each film thickness, we determined the phase velocity in the CPW with an accuracy better than 0.1% by least-squares fitting of a theoretical S_{21} curve based on the transmission matrix to the experimental data at the base temperatures. Not only the film-thickness dependence but also the temperature dependence of the resonators are explained by taking into account the kinetic inductance of the CPW center conductor.

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